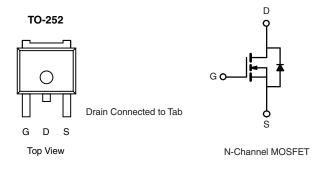
SQD25N06-22L



Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.022			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.033			
I _D (A)	25			
Configuration	Single			



FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- Package with Low Thermal Resistance
- 100 % $\rm R_g$ and UIS Tested
- AEC-Q101 Qualified^d
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD25N06-22L-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Drain Current	T _C = 25 °C ^a	I_	25		
Continuous Drain Current	T _C = 125 °C	l I _D	20		
Continuous Source Current (Diode Conduction) ^a	I _S	25	А		
Pulsed Drain Currentb		I _{DM}	100		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	24		
Single Pulse Avalanche Energy		E _{AS}	28	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	62	w	
	T _C = 125 °C	P _D	20	٧٧	
Operating Junction and Storage Temperature Range)	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	2.4	0/10	

Notes

a. Package limited.

b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

c. When mounted on 1" square PCB (Fr-4 material).

d. Parametric verification ongoing.

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SPECIFICATIONS ($T_C = 25 \ ^{\circ}C_{,}$, unless otherv	vise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•	•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		60	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$		2.0	2.5		
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1.0		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	25	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.018	0.022	Ω	
Drain-Source On-State Resistance ^a	В	$V_{GS} = 10 V$	I _D = 20 A, T _J = 125 °C	-	-	0.039		
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 20 A, T _J = 175 °C	-	-	0.049		
		$V_{GS} = 4.5 V$	I _D = 20 A, T _J = 25 °C	-	0.027	0.033		
Forward Transconductance ^a	9 _{fs}	V _{DS}	= 15 V, I _D = 12 A	-	32	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	1580	1975		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	305	382	pF	
Reverse Transfer Capacitance	C _{rss}			-	130	163		
Total Gate Charge ^c	Qg			-	33	50		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 25 \text{ A}$	-	5.3	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	6.8	-		
Gate Resistance	R _g	f = 1 MHz		1.1	2.2	3.3	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	8	12		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 30 \text{ V}, \ R_{\text{L}} = 1.2 \ \Omega \\ I_{\text{D}} \cong 25 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	10	15	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	24	36		
Fall Time ^c	t _f			-	6	9		
Source-Drain Diode Ratings and Char	acteristics ^b					•		
Pulsed Current ^a	I _{SM}			-	-	100	Α	
Forward Voltage	V _{SD}	I _F = 25 A, V _{GS} = 0 V		-	0.9	1.5	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

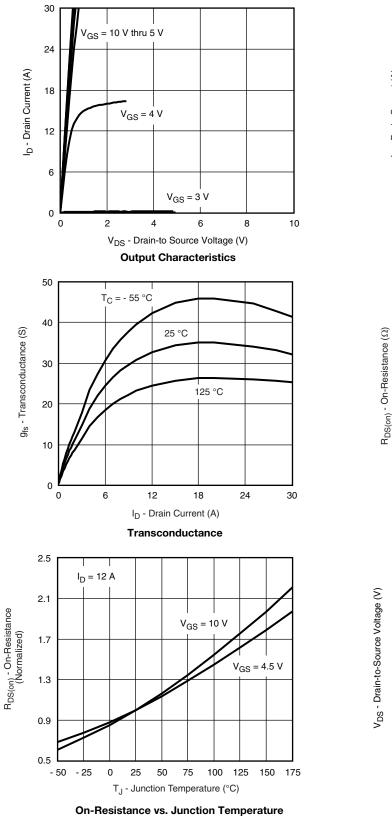
2

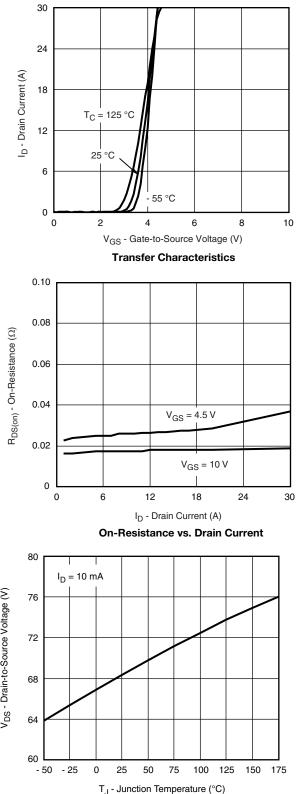
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)





Drain Source Breakdown vs. Junction Temperature

S11-2046-Rev. C, 24-Oct-11

Document Number: 65360

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

100 0.25 T_J = 150 °C 10 0.20 R_{DS(on)} - On-Resistance I_S - Source Current (A) T_J = 25 °C 0.15 1 0.10 0.1 $T_J = 150 \ ^\circ C$ 0.05 0.01 $T_J = 25 \ ^{\circ}C$ 0.001 0 0 0.2 0.4 0.6 0.8 1.0 1.2 0 2 4 6 8 10 V_{GS} - Gate-to-Source Voltage (V) V_{SD} - Source-to-Drain Voltage (V) Source Drain Diode Forward Voltage **On-Resistance vs. Gate-to-Source Voltage** 3000 10 I_D = 25 A 2500 V_{GS} - Gate-to-Source Voltage (V) 8 C - Capacitance (pF) $V_{DS} = 30 V$ 2000 Ciss 6 1500 4 1000 Coss 2 500 C_{rss} 0 0 5 10 15 25 35 0 20 30 10 30 40 50 60 0 20 V_{DS} - Drain-to-Source Voltage (V) Q_q - Total Gate Charge (nC) Capacitance **Gate Charge** 0.6 0.3 V_{GS(th)} - Variance (V) 0 - 0.3 $I_D = 5 \text{ mA}$ - 0.6 I_D = 250 μA - 0.9 - 1.2 - 50 - 25 0 25 50 75 100 125 150 175 T_J - Temperature (°C) **Threshold Voltage**



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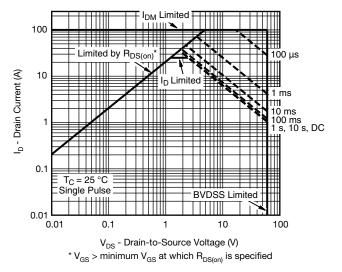
Document Number: 65360



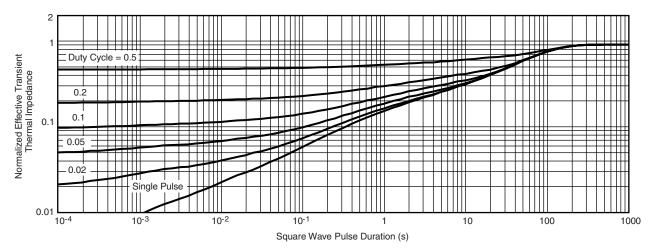
SQD25N06-22L

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

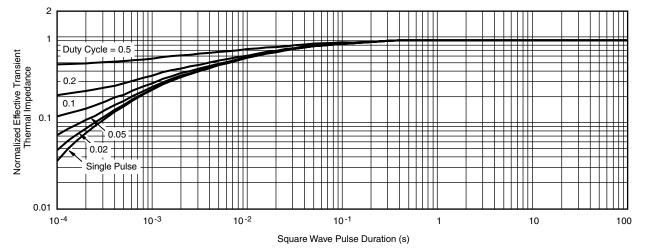


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

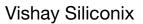
• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

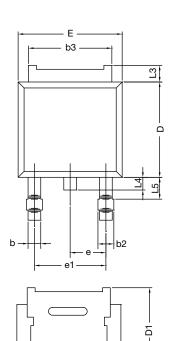
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65360.







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TO-252AA Case Outline

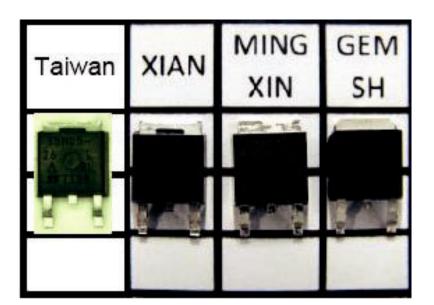
	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0359-Rev. O, 03-Jun-13 DWG: 5347					

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Notes

• Dimension L3 is for reference only.

• Xi'an, Mingxin, and GEM SH actual photo.



Revision: 03-Jun-13

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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